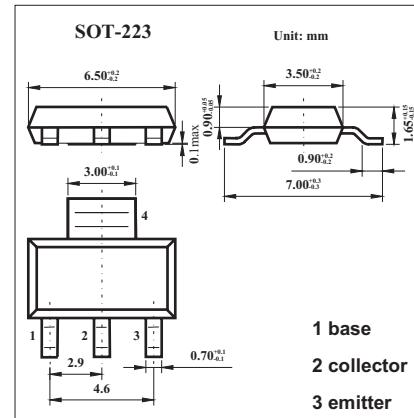


**PNP Silicon Planar Medium
Power High Gain Transistor
FZT788B**

■ Features

- Low equivalent on-resistance; $R_{CE(sat)}$ 93m Ω at 3A.
- Gain of 300 at $I_C=2$ Amps and Very low saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-15	V
Collector-emitter voltage	V _{C EO}	-15	V
Emitter-base voltage	V _{EBO}	-5	V
Continuous collector current	I _{CM}	-8	A
Peak pulse current	I _C	-3	A
Power dissipation	P _{tot}	2	W
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

FZT788B

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	Ic=-100µA	-15			V
Collector-emitter breakdown voltage *	V(BR)CEO	Ic=-10mA	-15			V
Emitter-base breakdown voltage	V(BR)EBO	Ie=-100µA	-5			V
Collector-base cut-off current	IcBO	Vcb=-10V			-0.1	µA
Emitter Cut-Off Current	IeBO	Veb=-4V			-0.1	µA
Collector-emitter saturation voltage *	Vce(sat)	Ic=-0.5A, Ib=-2.5mA Ic=-1A, Ib=-5mA Ic=-2A, Ib=-10mA Ic=-3A, Ib=-50mA			-0.15 -0.25 -0.45 -0.5	V
Base-emitter saturation voltage *	Vbe(sat)	Ic=-1A, Ib=-5mA			-0.9	V
Base-emitter ON voltage *	Vbe(on)	Ic=-1A, Vce=-2V		-0.75		V
Static Forward Current Transfer Ratio	hFE	Ic=-10mA, Vce=-2V *	500		1500	
		Ic=-1A, Vce=-2V*	400			
		Ic=-2A, Vce=-2V*	300			
		Ic=-6A, Vce=-2V*	150			
Transitional frequency	fT	Ic=-50mA, Vce=-5V, f=50MHz	100			MHz
Input capacitance	Cibo	Veb=-0.5V, f=1MHz		225		pF
Output capacitance	Cobo	Vcb=-10V, f=1MHz		25		pF
Turn-on time	t(on)	Ic=-500mA, Vcc=-10V Ib1=Ib2=-50mA		35		ns
Turn-off time	t(off)			400		ns

* Pulse test: tp = 300 µs; d ≤ 0.02.

■ Marking

Marking	FZT788B
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